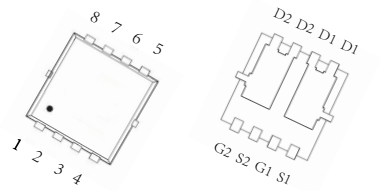
GPM800NP06LNB

60V N- and P-Channel MOSFET

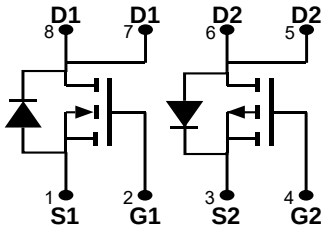
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	30mΩ@10V	15A
	37mΩ@4.5V	
-60V	62mΩ@-10V	-11A
	75mΩ@-4.5V	

PDFN3.3X3.3-8L



Schematic diagram



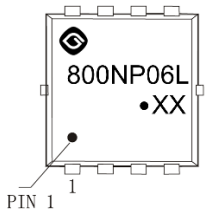
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

Application

- PWM Applications
- Loas Switch
- Power Management

MARKING:



800NP06L = Device Code
XX = Data Code
Solid Dot = Green Device Indicater

ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	NMOS	PMOS	Unit
Drain - Source Voltage		V_{DS}	60	-60	V
Gate - Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current[1,5]	T_A = 25℃	I_D	15	-11	A
Pulsed Drain Current[2]		I_{DM}	60	-44	A
Power Dissipation[4,5]		P_D	1.5	1.5	W
Thermal Resistance from Junction to Ambient[5]		$R_{\theta JA}$	80	80	℃/W
Junction Temperature		T_J	150	150	℃
Storage Temperature		T_{STG}	-55~ +150	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25℃ unless otherwise noted)

NMOS:

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.7	3	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 4.3A		30	40	mΩ
		V_{GS} = 4.5V, I_D = 3.9A		37	55	
Forward tranconductance	g_{FS}	V_{DS} = 6V, I_D = 5A	5			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz		974		pF
Output Capacitance	C_{oss}			62		
Reverse Transfer Capacitance	C_{rss}			53		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		1.8		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 30V, V_{GS} = 10V, I_D = 5A		20		nC
Gate-source Charge	Q_{gs}			2.7		
Gate-drain Charge	Q_{gd}			4.7		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 30V, V_{GS} = 10V, R_L = 6Ω R_G = 2Ω		5.6		ns
Turn-on Rise Time	t_r			4.8		
Turn-off Delay Time	$t_{d(off)}$			26		
Turn-off Fall Time	t_f			3.5		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = 10A			1.2	V

PMOS:

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -48V, V_{GS} = 0V			-1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-2	-3	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -3.1A		62	80	mΩ
		V_{GS} = -4.5V, I_D = -2.0A		75	110	
Forward tranconductance	g_{FS}	V_{DS} = -6V, I_D = -4A	5			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz		892		pF
Output Capacitance	C_{oss}			72		
Reverse Transfer Capacitance	C_{rss}			61		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = -30V, V_{GS} = -10V, I_D = -4A		20		nC
Gate-source Charge	Q_{gs}			2.7		
Gate-drain Charge	Q_{gd}			5		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -30V, V_{GS} = -10V, R_L = 7.5Ω R_G = 3Ω		10		ns
Turn-on Rise Time	t_r			12		
Turn-off Delay Time	$t_{d(off)}$			24		
Turn-off Fall Time	t_f			10		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = -6A			-1.2	V

Notes :

1.The maximum current rating is limited by package.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

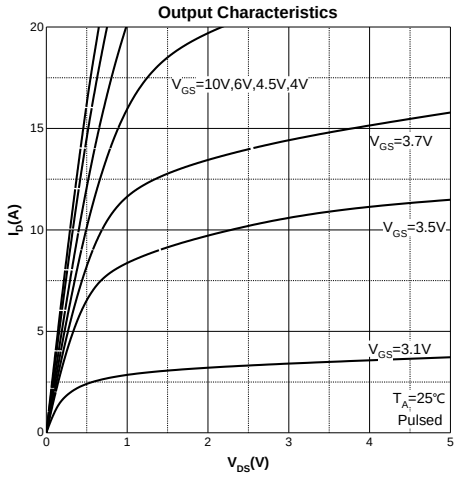
3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

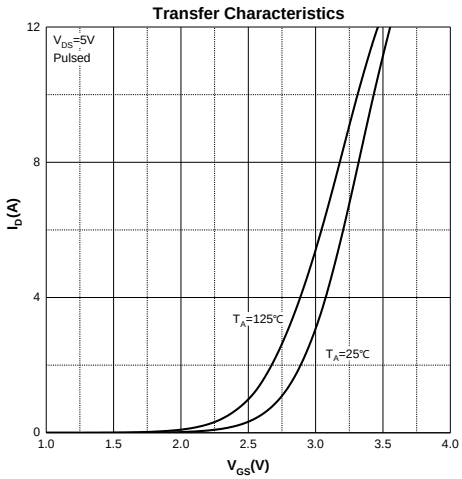
4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.

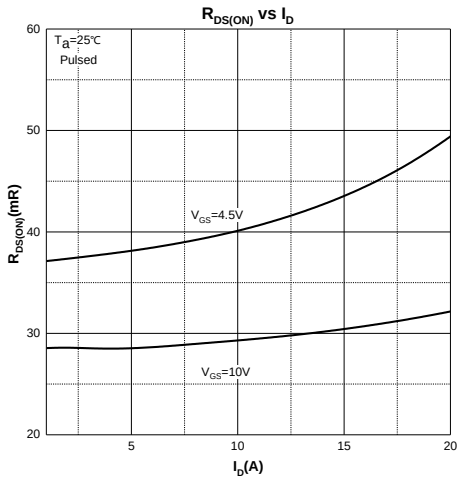
5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

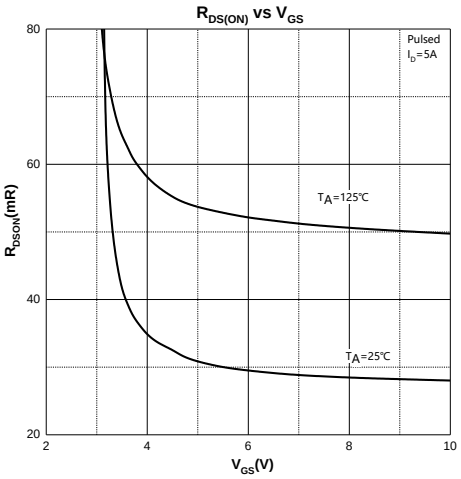
Typical Characteristics

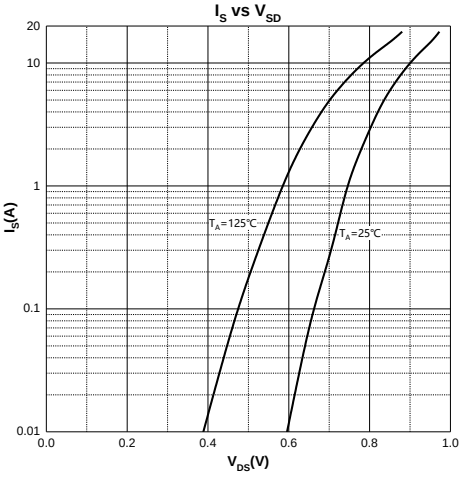
NMOS:

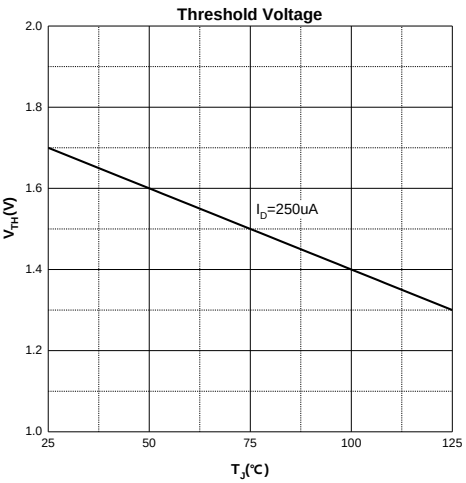






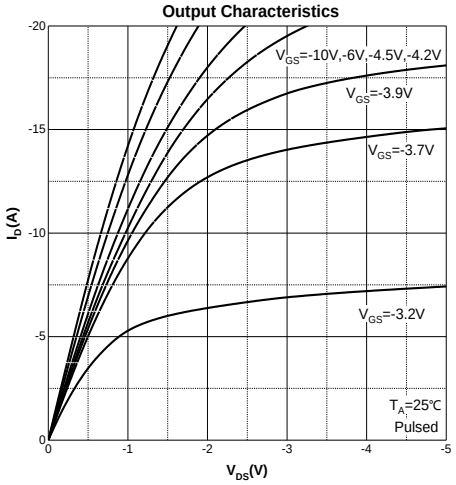


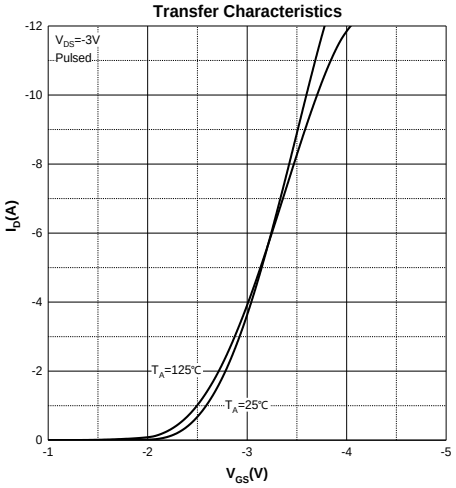


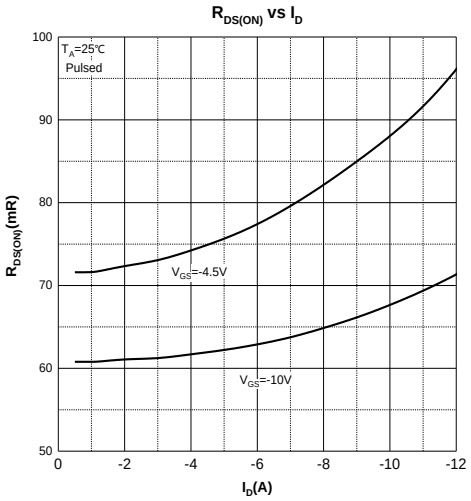


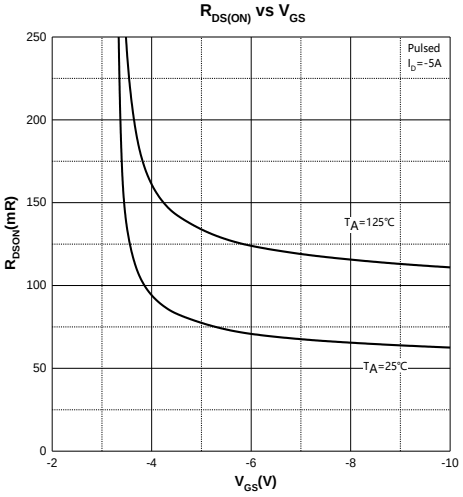
Typical Characteristics

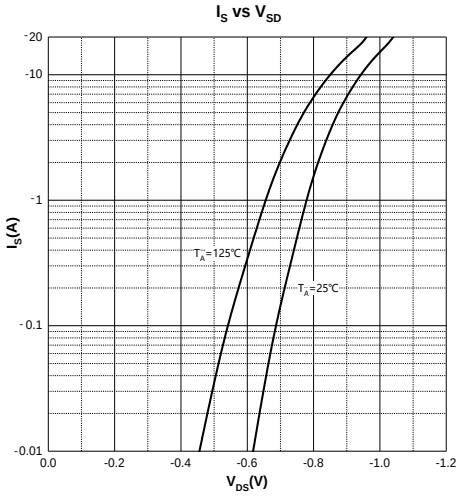
PMOS:

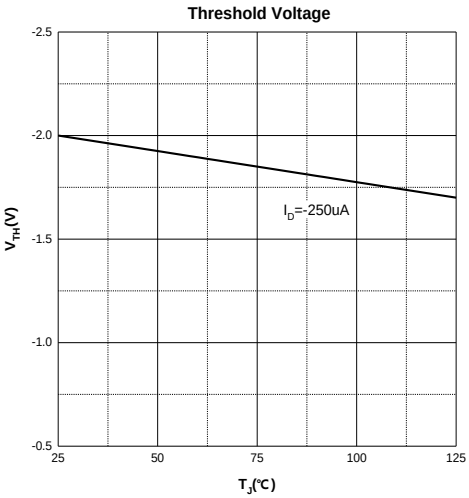




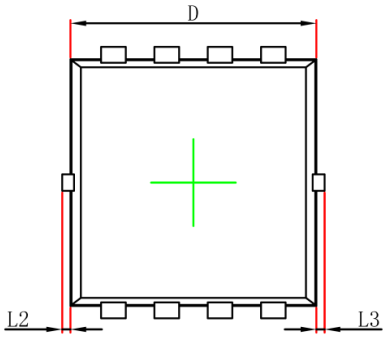




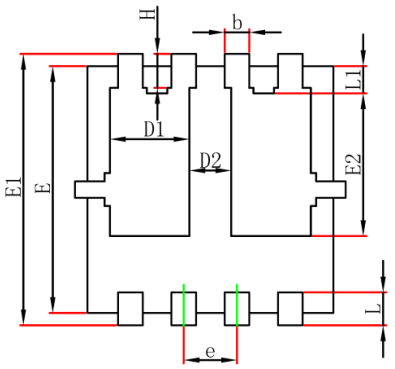




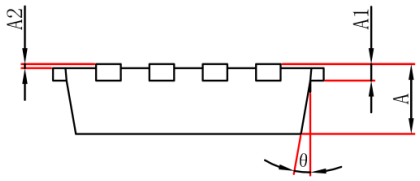
PDFN3.3X3.3-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.152REF		0.006REF	
A2	0.000	0.050	0.000	0.002
D	2.900	3.200	0.114	0.126
D1	0.935	1.135	0.037	0.045
D2	0.280	0.480	0.011	0.019
E	2.900	3.200	0.114	0.126
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0.000	0.100	0.000	0.004
L3	0.000	0.100	0.000	0.004
H	0.315	0.515	0.012	0.020
θ	0°	12°	0°	12°